Abstracts

A 900 MHz HBT power amplifier MMICs with 55% efficiency, at 3.3 V operation

H. Asano, S. Hara and S. Komai. "A 900 MHz HBT power amplifier MMICs with 55% efficiency, at 3.3 V operation." 1998 MTT-S International Microwave Symposium Digest 98.1 (1998 Vol. I [MWSYM]): 205-208.

A 3.3 volt GSM class V power amplifier MMIC has been developed by using AlGaAs/GaAs HBTs and flip chip bonding technology. The amplifier has an output power of 32 dBm and a power added efficiency of 55%. The HBT amplifier inherently requires no negative bias and has very low leak current, 2nA. Th MMIC is assembled to small and low profile package (6.35/spl times/6.35/spl times/1.05 mm).

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